

L Number	Hits	Search Text	DB	Time stamp
1	852	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor))	USPAT	2003/10/30 14:31
2	28	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor)) and (second adj power)	USPAT	2003/10/30 14:31
3	92	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor)) and anti\$!reflective	USPAT	2003/10/30 14:31
4	680	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor)) and (photo\$!resist or resist)	USPAT	2003/10/30 14:31
5	1	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor))	EPO; JPO; DERWENT	2003/10/30 14:32
6	357	semiconductor and plasma and power and (photo\$!resist or resist)	EPO; JPO; DERWENT	2003/10/30 14:32
7	9	(semiconductor and plasma and power and (photo\$!resist or resist)) and (anti\$!reflective or ARC!)	EPO; JPO; DERWENT	2003/10/30 14:33
8	10	(semiconductor and plasma and power and (photo\$!resist or resist)) and (anti\$!reflective or ARC! or BARC)	EPO; JPO; DERWENT	2003/10/30 14:33
-	6	("6489632") or ("6426016") or ("6355557") or ("6180533") or ("6074959") or ("6054377")).PN.	USPAT	2003/06/24 09:48
-	13	("6489632") or ("6426016") or ("6355557") or ("6180533") or ("6074959") or ("6054377") or ("5726499") or ("5710067") or ("5242532") or ("5242536") or ("5312717") or ("5662770") or ("5843226")).PN.	USPAT	2003/06/24 10:01
-	29912	semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))	USPAT	2003/06/24 10:04
-	15628	(semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))) and plasma	USPAT	2003/06/24 10:04
-	3739	(semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))) and (plasma same power)	USPAT	2003/06/24 10:05
-	3176	((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))) and (plasma same power)) and (Watt or W!)	USPAT	2003/06/24 10:04
-	19830	semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))	USPAT	2003/06/24 10:05

-	2821	((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power))	USPAT	2003/06/24 10:06
-	2421	((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and (Watt or W!)	USPAT	2003/06/24 10:07
-	1163	((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt	USPAT	2003/06/24 10:07
-	823	((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)	USPAT	2003/06/24 10:08
-	823	((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor	USPAT	2003/06/24 10:08
-	592	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor) and 438/\$.ccls.	USPAT	2003/10/30 14:17
-	38	(((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor) and 438/706.ccls.	USPAT	2003/06/24 10:12
-	33686	((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)	USPAT	2003/06/26 15:21
-	2089	((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) same power	USPAT	2003/06/26 15:22
-	1051	((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) same power) same (Cl?sub.2 or chlorine ro CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or Ar! or argon)	USPAT	2003/06/26 15:24
-	20	(((((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) same power) same (Cl?sub.2 or chlorine ro CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or Ar! or argon)) and (second adj power)	USPAT	2003/06/26 15:25